

TRENCHSTOP™ IGBT4 Low Power Chip

Features:

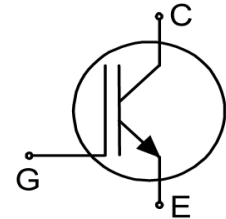
- 1200V trench & field stop technology
- Low switching losses
- Positive temperature coefficient
- Easy paralleling

Recommended for:

- Low / medium power modules

Applications:

- Low / medium power drives



Chip Type	V _{CE}	I _{CN}	Die Size	Package
IGC189T120T8RL	1200V	200A	13.62mm x 13.87mm	Sawn on foil

Mechanical Parameters

Die size	13.62 x 13.87		mm ²
Emitter pad size	See chip drawing		
Gate pad size	1.31 x 0.81		
Area total	188.91		
Silicon thickness	115		µm
Wafer size	200		mm
Maximum possible chips per wafer	125		
Passivation frontside	Photoimide		
Pad metal	3200nm AlSiCu		
Backside metal	Ni Ag – system To achieve a reliable solder connection it is strongly recommended not to consume the Ni layer completely during production process		
Die bond	Electrically conductive epoxy glue and soft solder		
Wire bond	Al, ≤500µm		
Reject ink dot size	Ø 0.65mm; max. 1.2mm		
Storage environment (<6 months)	for original and sealed MBB bags	Ambient atmosphere air, temperature 17°C – 25°C	
	for open MBB bags	Acc. IEC 62258-3; Section 9.4 Storage Environment.	

Maximum Ratings

In general, from reliability and lifetime point of view, the lower the operation junction temperature and/or the applied voltage, the greater the expected lifetime of any semiconductor device.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj}=25^{\circ}\text{C}$	V_{CE}	1200	V
DC collector current, limited by $T_{vj\text{ max}}^1$	I_C	-	A
Pulsed collector current, t_p limited by $T_{vj\text{ max}}^2$	$I_{C,puls}$	600	A
Gate-emitter voltage	V_{GE}	± 20	V
Junction temperature	T_{vj}	-40 ... +175	$^{\circ}\text{C}$
Operating junction temperature	$T_{vj\text{ op}}$	-40 ... +150	$^{\circ}\text{C}$
Short circuit data ^{1/2/3} $V_{GE}=15\text{V}$, $V_{CC}=800\text{V}$, $T_{vj}=150^{\circ}\text{C}$	t_{sc}	10	μs

Static Characteristics (tested on wafer), $T_{vj}=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0\text{V}$, $I_C=1\text{mA}$	1200	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE}=15\text{V}$, $I_C=60\text{A}$	1.11	1.19	1.27	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=7.4\text{mA}$, $V_{GE}=V_{CE}$	5.3	5.8	6.3	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1200\text{V}$, $V_{GE}=0\text{V}$	-	-	2.6	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0\text{V}$, $V_{GE}=20\text{V}$	-	-	120	nA
Integrated gate resistor	r_G		-	3.5	-	Ω

Electrical Characteristics ²

Parameter	Symbol	Conditions	Value			Unit	
			min.	typ.	max.		
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE}=15\text{V}$, $I_C=200\text{A}$	$T_{vj}=25^{\circ}\text{C}$	1.55	1.8	2.05	V
			$T_{vj}=150^{\circ}\text{C}$	-	2.1	-	
Input capacitance	C_{ies}	$V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$, $f=1\text{MHz}$ $T_{vj}=25^{\circ}\text{C}$	-	14000	-	pF	
Reverse transfer capacitance	C_{res}		-	500	-		

¹ Depending on thermal properties of assembly.

² Not subject to production test - verified by design/characterization.

³ Allowed number of short circuits: <1000; time between short circuits: >1s.